

### 2N5086/2N5087/MMBT5087

#### **PNP General Purpose Amplifier**

• This device is designed for low level, high gain, low noise general purpose amplifier applications at collector currents to 50mA.





1. Emitter 2. Base 3. Collector

1. Base 2. Emitter 3. Collector

#### **Absolute Maximum Ratings\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-3.0	V
I <sub>C</sub>	Collector current - Continuous	-100	mA
T <sub>J</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55 ~ +150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Parameter	Test Condition		Min.	Max.	Units
teristics			•		
Collector-Emitter Breakdown Voltage *	$I_C = -1.0 \text{mA}, I_B = 0$		-50		V
Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$		-50		V
Collector Cutoff Current	$V_{CB} = -10V, I_E = 0$			-10	nA
	$V_{CB} = -35V, I_{E} = 0$			-50	nA
Emitter Cutoff Current	$V_{EB} = -3.0V, I_{C} = 0$			-50	nA
teristics					
DC Current Gain	$I_C = -100 \mu A, V_{CE} = -5.0 V$	5086	150	500	
		5087	250	800	
	$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$	5086	150		
		5087	250		
	$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$	5086	150		
		5087	250		
Collector-Emitter Saturation Voltage	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$			-0.3	V
Base-Emitter On Voltage	$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$			-0.85	V
al Characteristics			•		•
Current Gain Bandwidth Product	$I_C = -500\mu A$ , $V_{CE} = -5.0V$ , $f = 20MHz$		40		MHz
Collector-Base Capacitance	$V_{CB} = -5.0V$ , $I_F = 0$ , $f = 100KHz$			4.0	рF
Small-Signal Current Gain	$I_C = -1.0 \text{mA}, V_{CF} = -5.0 \text{V},$	5086	150	600	
	f = 1.0KHz	5087	250	900	
Noise Figure	$I_C = -100 \mu A, V_{CE} = -5.0 V$	5086		3.0	dB
	$R_S = 3.0k\Omega$ , $f = 1.0KHz$	5087		2.0	dB
	I <sub>C</sub> = -20μA, V <sub>CE</sub> = -5.0V	5086		3.0	dB
	$R_S = 10k\Omega$	5087		2.0	dB
	f = 10Hz to 15.7KHz				
	teristics  Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Collector Cutoff Current  Emitter Cutoff Current  teristics  DC Current Gain  Collector-Emitter Saturation Voltage Base-Emitter On Voltage  al Characteristics  Current Gain Bandwidth Product Collector-Base Capacitance Small-Signal Current Gain	teristicsCollector-Emitter Breakdown Voltage * $I_C = -1.0 \text{mA}$ , $I_B = 0$ Collector-Base Breakdown Voltage $I_C = -100 \mu \text{A}$ , $I_E = 0$ Collector Cutoff Current $V_{CB} = -10 \text{V}$ , $I_E = 0$ Emitter Cutoff Current $V_{CB} = -3.0 \text{V}$ , $I_C = 0$ teristics $I_C = -100 \mu \text{A}$ , $V_{CE} = -5.0 \text{V}$ DC Current Gain $I_C = -10 \text{mA}$ , $V_{CE} = -5.0 \text{V}$ $I_C = -10 \text{mA}$ , $V_{CE} = -5.0 \text{V}$ Collector-Emitter Saturation Voltage $I_C = -10 \text{mA}$ , $I_C = -1.0 \text{mA}$ Base-Emitter On Voltage $I_C = -10 \text{mA}$ , $I_C = -5.0 \text{V}$ al Characteristics $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C = -1.0 \text{mA}$ , $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C = -1.0 \text{mA}$ , $I_C = -1.$	teristics           Collector-Emitter Breakdown Voltage $I_C = -1.0 \text{mA}$ , $I_B = 0$ Collector-Base Breakdown Voltage $I_C = -100 \mu \text{A}$ , $I_E = 0$ Collector Cutoff Current $V_{CB} = -10 \text{V}$ , $I_E = 0$ Emitter Cutoff Current $V_{EB} = -3.0 \text{V}$ , $I_C = 0$ teristics $I_C = -100 \mu \text{A}$ , $V_{CE} = -5.0 \text{V}$ 5086           DC Current Gain $I_C = -100 \mu \text{A}$ , $V_{CE} = -5.0 \text{V}$ 5086 $I_C = -1.0 \text{mA}$ , $I_C = -1.0 \text{mA}$ , $I_C = -1.0 \text{mA}$ 5087 $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ 5086 $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ 5086 $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ 5086 $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ 5086 $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ 5087 $I_C = -1.0 \text{mA}$ , $I_C = -5.0 \text{V}$ , $I_C =$	Teristics   Collector-Emitter Breakdown Voltage *   I_C = -1.0mA, I_B = 0   -50	teristics           Collector-Emitter Breakdown Voltage * $I_C = -1.0 \text{mA}$ , $I_B = 0$ -50           Collector-Base Breakdown Voltage * $I_C = -100 \mu A$ , $I_E = 0$ -50           Collector Cutoff Current * $V_{CB} = -10 V$ , $I_E = 0$ -10 $V_{CB} = -35 V$ , $I_E = 0$ -50           Emitter Cutoff Current * $V_{EB} = -3.0 V$ , $I_C = 0$ -50           teristics           DC Current Gain * $I_C = -100 \mu A$ , $V_{CE} = -5.0 V$ 5086 150 5087 250 800 $I_C = -1.0 mA$ , $V_{CE} = -5.0 V$ 5086 150 5087 250 $I_C = -10 mA$ , $V_{CE} = -5.0 V$ 5086 150 5087 250 $I_C = -10 mA$ , $I_B = -1.0 mA         -0.3           Base-Emitter On Voltage *         I_C = -10 mA, I_B = -1.0 mA         -0.3           Base-Emitter On Voltage *         I_C = -1.0 mA, V_{CE} = -5.0 V         -5.085           Current Gain Bandwidth Product I_C = -5.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0 V, I_C = 0.0 \mu A, I_C = -5.0$

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ınermaı	Characteristics T <sub>2</sub> =25°C unless otherwise noted

Symbol	Parameter	Ma		
		2N5086 2N5087	*MMBT5087	Units
P <sub>D</sub>	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup> Device mounted on FR-4 PCB 1.6" × 1.6" × 0.06."

# **Typical Characteristics**

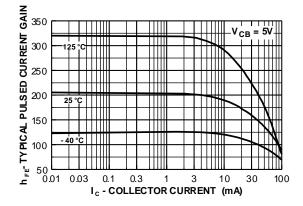


Figure 1. Typical Pulsed Current Gain vs Collector Current

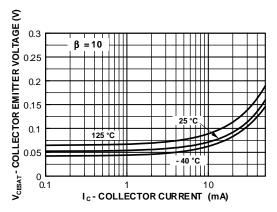


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

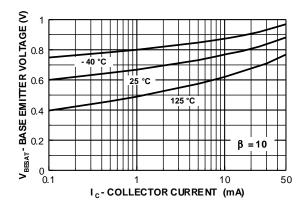


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

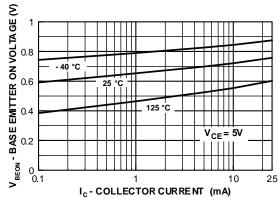


Figure 4. Base-Emitter On Voltage vs Collector Current

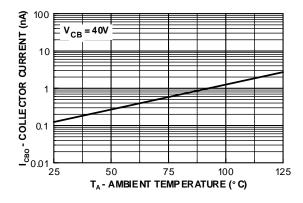


Figure 5. Collector Cutoff Current vs Ambient Temperature

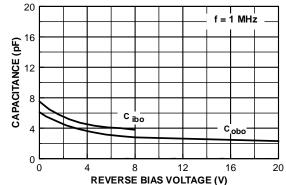


Figure 6. Input and Output Capacitance vs Reverse Voltag

## Typical Characteristics(Continuce)

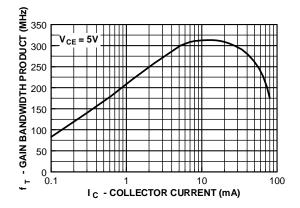


Figure 7. Gain Bandwidth Product vs Collector Current

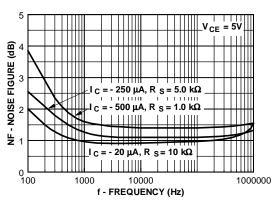


Figure 8. Noise Figure vs Frequency

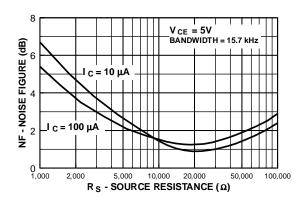


Figure 9. Wideband Noise Frequency vs Source Resistance

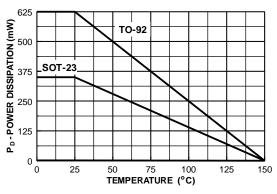


Figure 10. Power Dissipation vs Ambient Temperature

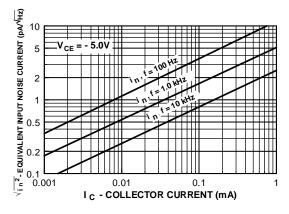


Figure 11. Equivalent Input Noise Current vs Collector Current

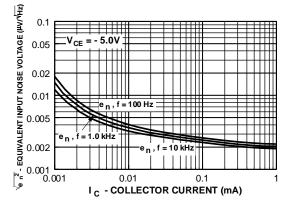


Figure 12. Equivalent Input Noise Voltage vs Collector Current

## Typical Characteristics (Continuce)

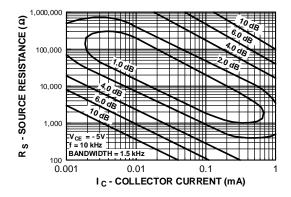


Figure 13. Contours of Constanct Narrow Band Noise Figure

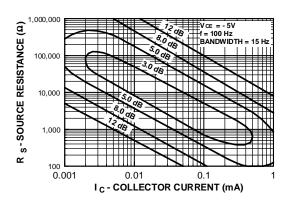


Figure 14. Contours of Constanct Narrow Band Noise Figure

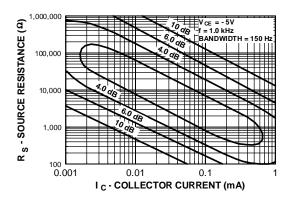


Figure 15. BContours of Constant Narrow Band Noise Figure

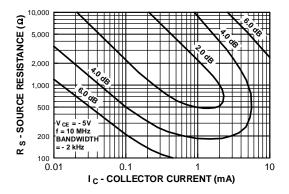
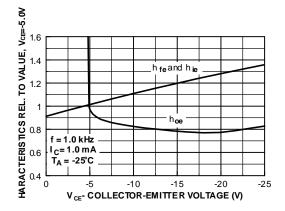
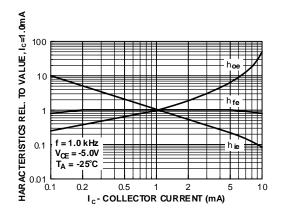


Figure 16. Contours of Constant Narrow Band Noisd Figure

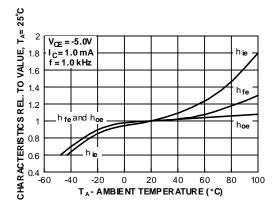
# **Typical Common Emitter Characteristics** (f = 1.0KHz)



**Typical Common Emitter Characteristics** 



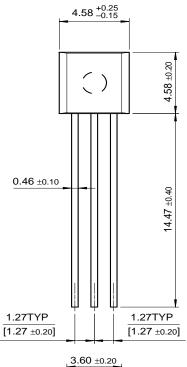
**Typical Common Emitter Characteristics** 

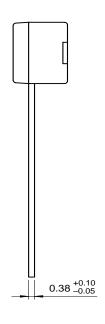


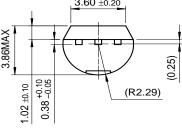
**Typical Common Emitter Characteristics** 

# **Package Dimensions**

TO-92

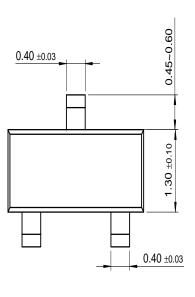


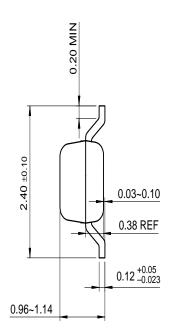


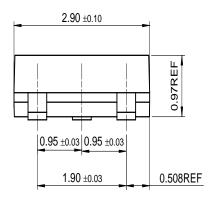


# Package Dimensions (Continued)

# SOT-23







Dimensions in Millimeters

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